## NSN 5961-01-448-3255

Fiig: A110a0

Thyristor Semiconductor Device - Page 1 of 1



View Online at https://aerobasegroup.com/nsn/5961-01-448-3255 **Inclosure Material:** Metal **Overall Length:** 1.646 inches **Overall Diameter:** 0.650 inches **Mounting Facility Quantity: Internal Configuration:** Junction contact Joint Electronic Device Engineering Council/jedec/case Outline Designation: To-48 **Mounting Method:** Threaded stud **Overall Width Across Flats:** Between 0.544 inches and 0.562 inches **Semiconductor Material:** Silicon **Voltage Rating In Volts Per Characteristic:** 650.0 forward voltage, peak and 50.0 emitter supply voltage **Current Rating Per Characteristic:** 250.00 amperes source cutoff current outside diameter **Power Rating Per Characteristic:** 40.0 watts small-signal input power, common-collector blank and 0.5 watts small-signal input power, common-collector universal **Maximum Operating Tempurature Per Measurement Point:** 115.0 degrees celsius case **Special Features:** Junction pattern arrangement: pnpn **Test Data Document:** 29357-43033-212-00481 drawing (this is the basic governing drawing, such as a contractor drawing, original equipment manufacturer drawing, etc.; excludes any specification, standard or other document that may be referenced in a basic governing drawing) **Terminal Type And Quantity:** 2 tab, solder lug and 1 threaded stud Shelf Life: N/a **Unit Of Measure: Demilitarization:** No